

PRELIMINARY M5M51T08BP,FP,VP,RV-55SL,-70SL,-10SL

Notice: This is not a final specification.
Some parametric limits are subject to change.

1048576-BIT(131072-WORD BY 8-BIT)CMOS STATIC RAM

DESCRIPTION

The M5M51T08BP,FP,VP,RV are a 1048576-bit CMOS static RAM organized as 131072 word by 8-bit which are fabricated using high-performance quadruple-polysilicon CMOS technology. The use of thin film transistor(TFT) load cells and CMOS periphery result in a high density, ultra low power and high reliability static RAM.

They are low standby current and low operation current and ideal for the battery back-up application.

The M5M51T08B are offered in a 32-pin plastic dual-in-line package (DIP), 32-pin plastic small outline package (SOP), as well as 32-pin thin small outline package (TSOP), providing high board level packing densities. Two types of TSOP packages are available. M5M51T08BVP (normal lead bend type package), M5M51T08BRV (reverse lead bend type package). Using both two types makes it easy to design a printed circuit board.

FEATURES

Type name	Access time (max)	Power supply current	
		Active (max)	Stand-by (max)
M5M51T08BP, FP, VP, RV-55SL	55ns	15mA (1MHz)	10 μ A (V _{CC} = 5.5V)
M5M51T08BP, FP, VP, RV-70SL	70ns		0.05 μ A (V _{CC} = 3.0V, typ)
M5M51T08BP, FP, VP, RV-10SL	100ns		

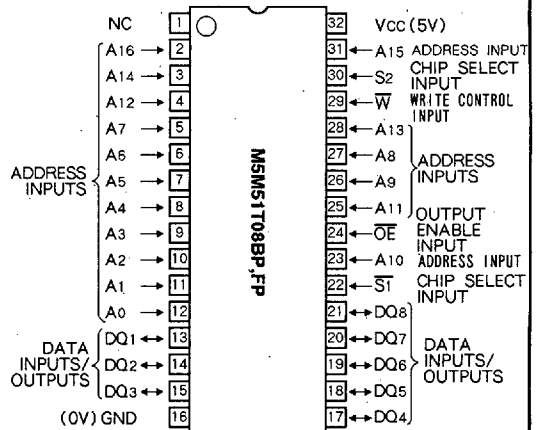
- Single +5V power supply
- Low stand-by current 0.05 μ A (typ)
- Directly TTL compatible: All inputs and outputs
- Easy memory expansion and power down by \bar{S}_1, \bar{S}_2
- Data hold on +2V power supply
- Three-state outputs: OR-tie capability
- \bar{OE} prevents data contention in the I/O bus
- Common data I/O
- Package

M5M51T08BP.....	32 pin 600 mil DIP
M5M51T08BFP.....	32 pin 525 mil SOP
M5M51T08BVP, RV.....	32 pin 8 x 20mm ² TSOP

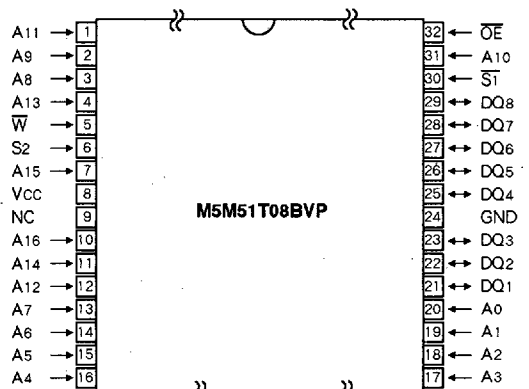
APPLICATION

Small capacity memory units

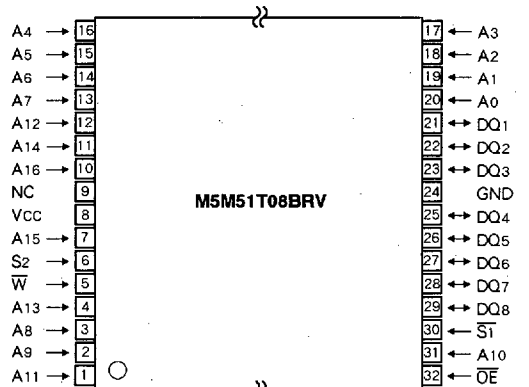
PIN CONFIGURATION (TOP VIEW)



Outline 32P4 (P)
32P2M-A (FP)



Outline 32P3H-E



Outline 32P3H-F

NC: NO CONNECTION